



INTERNSHIP PROGRAM FOR INTERNATIONAL STUDENTS

INTERNSHIP SUBJECT FORM



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| Name of the Host Laboratory | Laboratoire des Solides Irradies |
| Website of the Host Laboratory | https://portail.polytechnique.edu/lsi/en |
| Research Group | Materials Science Theory: https://portail.polytechnique.edu/lsi/en/research/materials-science-theory |
| Internship Supervisor | Jelena Sjakste |
| Internship Subject | Hot electron relaxation in 3D and 2D semiconductors: confinement and screening effects, a theoretical study. |
| Student's level | <input type="checkbox"/> Advanced Undergraduate Students (3 rd or 4 th year) <input checked="" type="checkbox"/> Master's students (1 st or 2 nd year) <input checked="" type="checkbox"/> PhD students |
| Proposed Duration | <input type="checkbox"/> 3 months <input checked="" type="checkbox"/> 4 months <input checked="" type="checkbox"/> 5 months <input checked="" type="checkbox"/> 6 months |
| Prerequisites | The proposed internship subject requires an understanding of quantum mechanics and solid state physics. It will involve theoretical as well as computational work, so some ability and willingness to program is essential. Some experience in computers with linux operating system is a plus, as well as some notions in Fortran. Previous experience in density functional theory is a plus, but is not mandatory. |
| Internship description (max. 15 lines) | <p>Interaction of excited electrons with lattice vibrations (phonons) plays a central role in nanoelectronics, for optoelectronic devices, photovoltaic and thermoelectric materials [1,2]. Recently, we developed an approach which allows to describe hot-electron relaxation dynamics and to interpret time- energy- and angle-resolved photoemission experiments [1,2].</p> <p>During this internship, we propose to study, using the methods based on Density Functional Theory, the atomic structure, the electronic and vibrational properties, and the electron-phonon coupling coefficients and hot electron relaxation dynamics in a 3D and 2D semiconductors. The work will be performed in close link with ongoing experiments.</p> <p>[1] Z. Chen, C. Giorgetti, J. Sjakste, R. Cabouat, V. Véniard, Z. Zhang, A. Taleb-Ibrahimi, E. Papalazarou, M. Marsi, A. Shukla, J. Peretti, L. Perfetti, <i>Ultrafast electron dynamics reveal the high potential of InSe for hot-carrier optoelectronics</i>, Phys. Rev. B 97, 241201(R) (2018).</p> <p>[2] J. Sjakste, K.Tanimura, G. Barbarino, L. Perfetti, N. Vast, <i>Hot electron relaxation dynamics in semiconductors: assessing the strength of the electron-phonon coupling from the theoretical and experimental viewpoints</i>, J. of Phys.: Cond. Mat, 30, 53001 (2018).</p> |

The boxes marked with cross implies eligible